

52. (Amended) The [electrode] dynamic random access memory device as specified in Claim 51, wherein said second portion and said third portion are different materials.

53. (Amended) The [electrode]dynamic random access memory device as specified in Claim 52, wherein said first portion and said third portion are different materials.

105. (Amended) A dynamic random access memory device comprising:
a capacitor including an electrode which comprises:
a) a first portion formed in an insulative layer having an upper surface;
b) a second portion overlying the first portion and having a sidewall substantially flush with the upper surface; and
c) a third portion overlying the second portion and, extending above and below the upper surface of the insulative layer, and including a recess, wherein the first portion and the second portion are different materials.

106. (Amended) The [electrode of] dynamic random access memory device as specified in Claim 105, wherein the second portion and the third portion are different materials.

107. (Amended) The [electrode of] dynamic random access memory device as specified in Claim 105, wherein the first portion and the third portion are different materials.

113. (Amended) The electrode of Claim 112, wherein the contact contacts the diffusion barrier portion, and the diffusion barrier portion contacts the oxidation resistant portion.